COMMODORE SEMICONDUCTOR GROUP

a division of Commodore Business Machines, Inc. 950 Rittenhouse Road, Nortistown, PA 19403 • 215/666-7950 • TWX 510-660-4168

NMOS

6508 MICROPROCESSOR WITH RAM AND I/O

DESCRIPTION

The 6508 is a low-cost microprocessor capable of solving a brand range of small-systems and peripheralcontrol problems at minimum cost to the user.

One full page (256 bytes) of RAM is located (on chip) concurrently at Page 0 and Page 1, allowing Zero Page Addressing and stack operations with no additional RAM.

An 8-bit Bi-Directional I/O Port is Icoated on-chip with the Output Register at Address 0001. The I/O Port is bit-by-bit programmable. The Data Direction register is at Address 0000.

The Three-State sixteen-bit Address Bus allows Direct Memory Accessing (DMA) and multi-processor systems sharing a common memory.

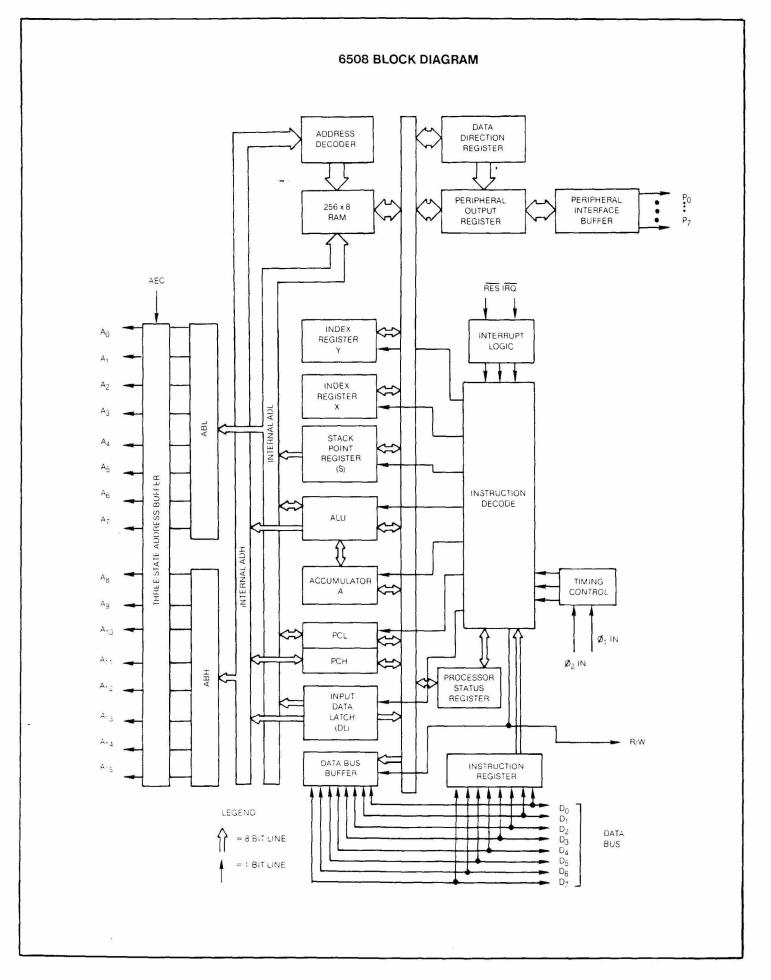
The internal processor architecture is identical to the Commodore Semiconductor Group 6502 to provide software compatibility.

FEATURES OF THE 6508...

- 8-Bit Bi-Directional I/O Port
- 256 Bytes fully Static RAM (internal)
- Single +5 volt supply
- N channel, silicon gate, depletion load technology
- Eight bit parallel processing
- 56 Instructions
- Decimal and binary arithmetic
- Thirteen addressing modes
- True indexing capability
- Programmable stack pointer
- Variable length stack
- Interrupt capability
- 8 Bit Bi-Directional Data Bus
- Addressable memory range of up to 65K bytes
- Direct memory access capability
- Bus compatible with M6800
- Pipeline architecture
- 1 MHz, 2MHz (Suffix "A"), and 3MHz (Suffix "B")
- Use with any type or speed memory.

6508 PIN CONFIGURATION

	-			
RES	1		40	Ø2IN
Ø1 IN	2		39	R/W
IRQ	3		38	DB ₀
AEC	4		37	DB1
VCC	5		36	DB_2
Au	6		35	DB_3
Α1	7		34	DB4
A ₂	8		33	DB ₅
A ₃	9	650	8 32	DB ₆
A ₄	10	000	31	DB7
A ₅	11		30	Po
A ₆	12		29	P1
A ₇	13		28	P ₂
A ₈	14		27	P ₃
A ₉	15		26	P ₄
A ₁₀	16		25	P ₅
A ₁₁	17		24	P ₆
A ₁₂	18		23	P ₇
A ₁₃	19		22	A15
VSS	20		21	A ₁₄



6508 CHARACTERISTICS

MAXIMUM RATINGS

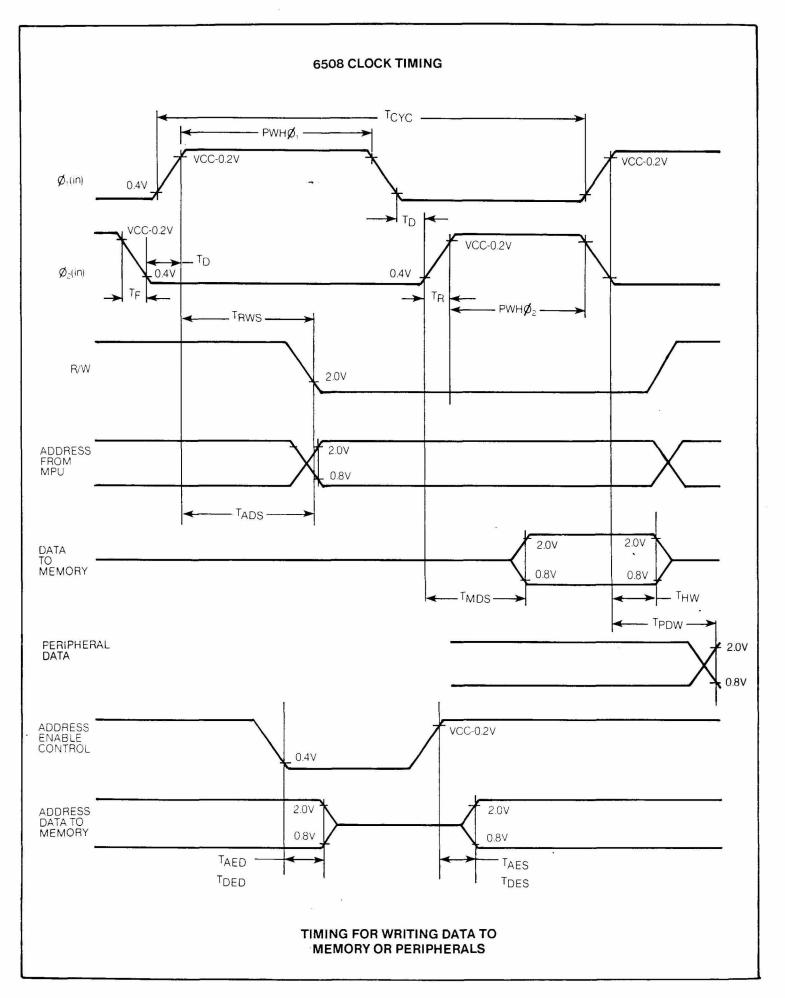
RATING	SYMBOL	VALUE	UNIT
SUPPLY VOLTAGE	V _{cc}	-0.3 to + 7.0	Vdc
INPUT VOLTAGE	Vin	-0.3 to + 7.0	Vdc
OPERATING TEMPERATURE	TA	0 to + 70	С°
STORAGE TEMPERATURE	TSTG	-55 to + 150	°C

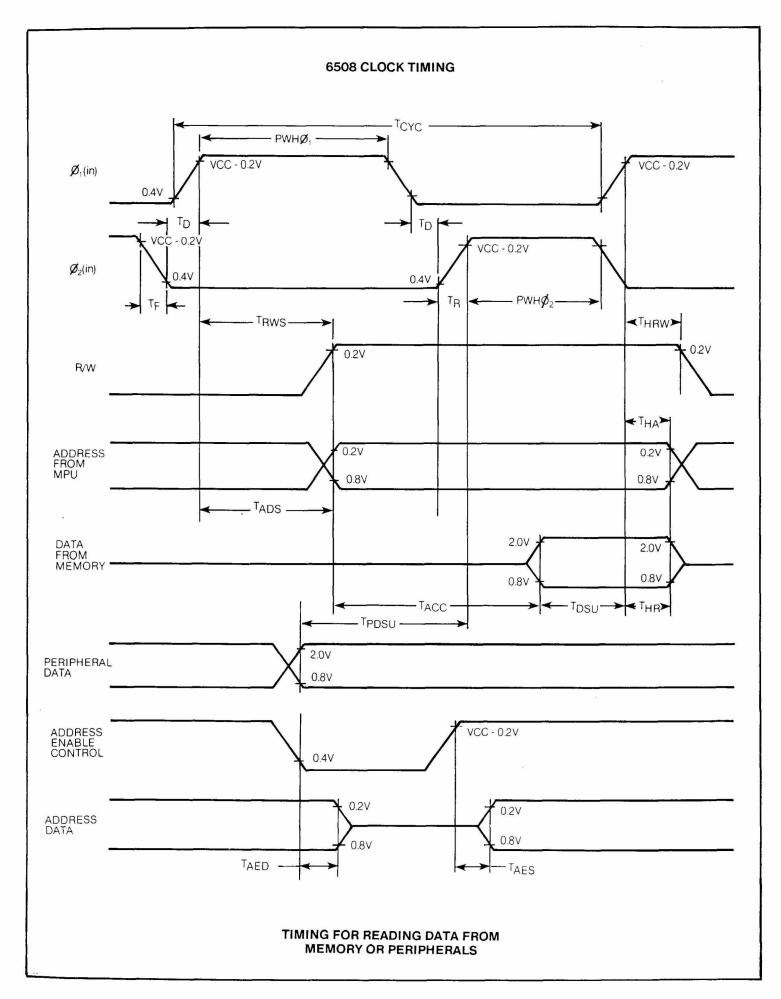
This device contains input protection against damage due to high static voltages or electric fields; however, precautions should be taken to avoid application of voltages higher than the maximum rating.

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ELECTRICAL CHARACTERISTICS (Vcc = 5.0V \pm 5%, Vss = 0, T_A = 0° to + 70°C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Input High Voltage					
Ø ₁ , Ø _{2(in)}	VIH	Vcc - 0.2	-	Vcc + 1.0V	Vdc
Input High Voltage	1		1		
RES, P ₀ -P ₇ IRQ, Data		Vss + 2.0	-		Vdc
Input Low Voltage					
Ø ₁ , Ø _{2(in)}	VIL	Vss - 0.3	-	Vss + 0.2	Vdc
RES, P ₀ -P ₇ IRQ, Data		-	-	Vss + 0.8	Vdc
Input Leakage Current					
(V _{in} = 0 to 5.25V, Vcc = 5.25V) Logic	lin		_	2.5	ALA
$\mathcal{O}_1, \mathcal{O}_2(in)$		-		100	μA
Three State (Off State) Input Current			1	()	
$(V_{in} = 0.4 \text{ to } 2.4 \text{V}, \text{Vcc} = 5.25 \text{V})$	170				
Data Lines	ITSI			10	Αų
Output High Voltage			1		
(I _{OH} = -100µAdc, Vcc = 4.75V) Data, A0-A15, R/W, P ₀ -P ₇	VOH	Vss + 2.4		-	Vdc
Out Low Voltage					
$(I_{OL} = 1.6 \text{mAdc}, \text{Vcc} = 4.75 \text{V})$ Data, A0-A15, R/W, P ₀ -P ₇	VOL	_	_	Vss + 0.4	Vdc
Power Supply Current	ICC	—	125	220	mA
Capacitance	С				pF
$V_{in} = 0$, $T_A = 25$ C, $f = 1$ MHz) Logic, P_0 - P_7	C _{in}	_	_	10	
Data		-	-	15	
A0-A15, R/W	Cout	-	-	12	
Ø,	CØ1		30	50	
\mathcal{O}_2	CØ2	-	50	80	1





AC CHARACTERISTICS

1 MHz TIMING

2 MHz TIMING

3 MHz TIMING

ELECTRICAL CHARACTERISTICS (VCC = 5V \pm 5%, VSS = 0V, T_A = 0 -70 C) Minimum Clock Frequency = 50 KHz

CLOCK TIMING

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNITS
Cycle Time	ТСҮС	1000	-		500	-		333	-	-	ns
Clock Pulse Width Ø1 (Measured at VCC – 0.2V) Ø2	PWH01 PWH02	430 470	_	-	215 235	=	-	150 160	_	_	ns
Fall Time. Rise Time (Measured from 0.2V to VCC - 0.2V);	TF. TR	_	_	25	_	-	15	_	-	15	ns
Delay Time between Clocks (Measured at 0.2V)	т _D	0	-	-	0	-	-	0	_	_	ns

READ/WRITE TIMING (LOAD=1 TTL)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNITS
Read/Write Setup Time from 6508	TRWS	-	100	300	-	100	150	-	80	125	ns
Address Setup Time from 6508	TADS	-	100	300	_	100	150		80	125	ns
Memory Read Access Time	TACC	-	-	575	-	—	300	-	-	170	ns
Data Stability Time Period	TDSU	100	-	_	50	—	-	30	-	-	ns
Data Hold Time-Read	T _{HR}	10	-	-	10	_	-	10	_		ns
Data Hold Time-Write	THW	10	30	-	10	30	-	10	_		ns
Data Setup Time from 6508	TMDS	~	150	200	-	75	100		70	100	ns
Address Hold Time	THA	10	30	_	10	30	-	10	30	-	ns
R/W Hold Time	THRW	10	30	-	10	30	-	10	30	-	ns
Delay Time. Ø2 negative transition to Peripheral Data valid	TPDW	_	_	1000	_	_	500	-	_	333	ns
Peripheral Data Setup Time	TPDSU	300	-		125	-	-	50	-	_	ns
Address Enable Setup Time	TAES	-	-	75			75	-		75	ns
Data Enable Setup Time	TDES	-	_	120			120	_	-	120	ns
Address Disable*	TAED	_	-	120	-	-	120	_	-	120	ns
Data Disable*	TDED	-	-	130	_	-	130	_	-	130	ns

* 1 TTL Load, CL = 30 pF

The 6508 requires a two phase non-overlapping clock that runs at the Vcc voltage level.

SIGNAL DESCRIPTION

Clocks $(\emptyset_1, \emptyset_2)$

The 6508 requires a two phase non-overlapping clock that runs at the Vcc voltage level.

Address Bus (A₀-A₁₅)

The three state outputs are TTL compatible, capable of driving one standard TTL load and 130 pf.

Data Bus (D₀-D₇)

Eight pins are used for the data bus. This is a Bi-Directional bus, transferring data to and from the device and peripherals. The outputs are tri-state buffers capable of driving one standard TTL load and 130 pf.

Reset

This input is used to reset or start the microprocessor from a power down condition. During the time that this line is held low, writing to or from the microprocessor is inhibited. When a positive edge is detected on the input, the microprocessor will immediately begin the reset sequence.

After a system initialization time of six clock cycles, the mask interrupt flag will be set and the microprocessor will load the program counter from the memory vector locations FFFC and FFFD. This is the start location for **program control**.

After Vcc reaches 4.75 volts in a power up routine, reset must be held low for at least two clock cycles. At this time the R/W signal will become valid.

When the reset signal goes high following these two clock cycles, the microprocessor will proceed with the normal reset procedure detailed above.

Interrupt Request (IRQ)

This TTL level input requests that an interrupt sequence begin within the microprocessor. The micorprocessor will complete the current instruction being executed before recognizing the request. At that time, the interrupt mask bit in the Status Code Register will be examined. If the interrupt mask flag is not set, the microprocessor will begin an interrupt sequence. The Program Counter and Processor Status Register are stored in the stack. The microprocessor will then set the interrupt mask flag high so that no further interrupts may occur. At the end of this cycle, the program counter low will be loaded from address FFFE, and program counter high from location FFFF, therefore transferring program control to the memory vector located at these addresses.

Address Enable Control (AEC)

The Address Bus, R/W and Data Bus are valid only when the Address Enable Control line is high. When low, the Address Bus, R/W and Data Bus are in a highimpedance state. This feature allows easy DMA and multiprocessor systems.

I/O Port (Po-P7)

Eight øins are used for the peripheral port, which can transfer data to or from peripheral devices. The Output Register is located in RAM at Address 0001, and the Data Direction Register is at Address 0000. The outputs are capable at driving one standard TTL load and 130 pf.

Read/Write (R/W)

This signal is generated by the microprocessor to control the direction of data transfers on the Data Bus. This line is high except when the microprocessor is writing to memory or a peripheral device.

ADDRESSING MODES

ACCUMULATOR ADDRESSING - This form of addressing is represented with a one byte instruction, implying an operation on the accumulator.

IMMEDIATE ADDRESSING - In immediate addressing, the operand is contained in the second byte of the instruction, with no further memory addressing required.

ABSOLUTE ADDRESSING - In absolute addressing, the second byte of the instruction specifies the eight low order bits of the effective address while the third byte specifies the eight high order bits. Thus, the absolute addressing mode allows access to the entire 65K bytes of addressable memory.

ZERO PAGE ADDRESSING - The zero page instructions allow for shorter code and execution times by only fetching the second byte of the instruction and assuming a zero high address byte. Careful use of the zero page can result in significant increase in code efficiency.

INDEXED ZERO PAGE ADDRESSING - (X, Y indexing) - This form of addressing is used in conjunction with the index register and is referred to as "Zero Page, X" or "Zero Page, Y." The effective address is calculated by adding the second byte to the contents of the index register. Since this is a form of "Zero Page" addressing, the content of the second byte references a location in page zero. Additionally, due to the "Zero Page" addressing nature of this mode, no carry is added to the high order 8 bits of memory and crossing of page boundaries does not occur.

INDEX ABSOLUTE ADDRESSING - (X, Y indexing) - This form of addressing is used in conjunction with X and Y index register and is referred to as "Absolute, X," and "Absolute, Y." The effective address is formed by adding the contents of X and Y to the address contained in the second and third bytes of the instruction. This mode allows the index register to contain the index or count value and the instruction to contain the base address. This type of indexing allows any location referencing and the index to modify multiple fields resulting in reduced coding and execution time.

INSTRUCTION SET – ALPHABETIC SEQUENCE

- ADS Add Memory to Accumulator with Carry
- AND "AND" Memory with Accumulator
- ASL Shift left One Bit (Memory or Accumulator)
- BCC Branch on Carry Clear
- BCS Branch on Carry Set
- BEQ Branch on Result Zero BIT
- Test Bits in Memory with Accumulator BMI Branch on Result Minus
- BNE Branch on Result not Zero
- BPL Branch on Result Plus
- BRK Force Break
- Branch on Overflow Clear BVC
- BVS Branch on Overflow Set
- Clear Carry Flag Clear Decimal Mode CLC
- CLD CLI Clear Interrupt Disable Bit
- CLV Clear Overflow Flag
- CMP Compare Memory and Accumulator
- CPX Compare Memory and Index X
- CPY Compare Memory and Index Y
- Decrement Memory by One Decrement Index X by One DEC
- DEX
- Decrement Index Y by One DEY
- EOR "Exclusive or" Memory with Accumulator

Increment Memory by One INC Increment Index X by One Increment Index Y by One INX

- INY
- JMP Jump to New Location
- Jump to New Location Saving Return Address **JSR**

IMPLIED ADDRESSING — In the implied addressing mode, the address containing the operand is implicitly stated in the operation code of the instruction.

RELATIVE ADDRESSING — Relative addressing is used only with branch instructions and establishes a destination for the conditional branch.

The second byte of the instruction becomes the operand which is an "Offset" added to the contents of the lower eight bits of the program counter when the counter is set at the next instruction. The range of the offset is -128 to +127 bytes from the next instruction.

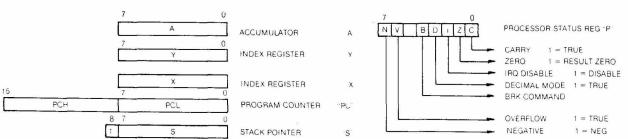
INDEXED INDIRECT ADDRESSING — In indexed indirect addressing (referred to as [Indirect, X]), the second byte of the instruction is added to the contents of the X index register, discarding the carry. The result of this addition points to a memory location on page zero whose contents is the low order eight bits of the effective address. The next memory location in page zero contains the high order eight bits of the effective address. Both memory locations specifying the high and low order bytes of the effective address must be in page zero.

INDIRECT INDEXED ADDRESSING — In indirect indexed addressing (referred to as [Indirect, Y]), the second byte of the instruction points to a memory location in page zero. The contents of this memory location is added to the contents of the Y index register, the result being the low order eight bits of the effective address. The carry from this addition is added to the contents of the next page zero memory location, the result being the high order eight bits of the effective address.

ABSOLUTE INDIRECT - The second byte of the instruction contains the low order eight bits of a memory location. The high order eight bits of that memory location is contained in the third byte of the instruction. The contents of the fully specified memory location is the low order byte of the effective address. The next memory location contains the high order byte of the effective address which is loaded into the sixteen bits of the program counter.

- LDA Load Accumulator with Memory
- LDX Load Index X with Memory
- I DY Load Index Y with Memory
- LSR Shift One Bit Right (Memory or Accumulator)
- NOP No Operation
- ORA "OR" Memory with Accumulator
- PHA Push Accumulator on Stack
- PHP Push Processor Status on Stack
- PIA Pull Accumulator from Stack PLP
 - Pull Processor Status from Stack
- ROL Rotate One Bit Left (Memory or Accumulator)
- Rotate One Bit Right (Memory or Accumulator) ROR **BTI** Return from Interrupt
- RTS Return from Subroutine
- Subtract Memory from Accumulator with Borrow SBC
- Set Carry Flag Set Decimal Mode SEC
- SED
- SEL Set Interrupt Disable Status
- STA Store Accumulator in Memory
- STX Store Index X in Memory Store Index Y in Memory STY
- TAX Transfer Accumulator to Index X TAY
- Transfer Accumulator to Index Y TSX Transfer Stack Pointer to Index X
- TXA Transfer Index X to Accumulator
- TXS Transfer Index X to Stack Register
- TYA Transfer Index Y to Accumulator

PROGRAMMING MODEL

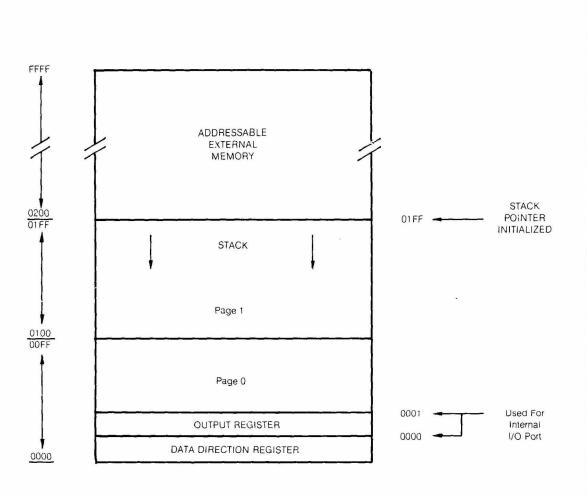


INSTRUCTION SET - OP CODES, Execution Time, Memory Requirements

			INSTRUCTIONS		IMM	EDIATE	AB	SOLUT	E	ERO F	MGE	A	CCUM.	1	PLIE	T	(INO.	XI	1	NDI. Y		Z PA	GE X	T	ABS.	(]	AE	BS. Y	Т	REL	ATIVE	T	NOIRE	CT	1	PAGE.	Y	CO	NDIT	ION	000	IES
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Note: Commodore Semiconductor Group cannot assume liability for the use of undefined OP Codes



6508 MEMORY MAP

APPLICATIONS NOTES

Locating the Output Register at the internal I/O Port in Page Zero enhances the powerful Zero Page Addressing instructions of the 6508.

By assigning the I/O Pins as inputs (using the Data Direction Register) the user has the ability to change the contents of address 0001 (the Output Register) using peripheral devices. The ability to change these contents using peripheral inputs, together with Zero Page Indirect Addressing instructions, allows novel and versatile programming techniques not possible earlier.

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